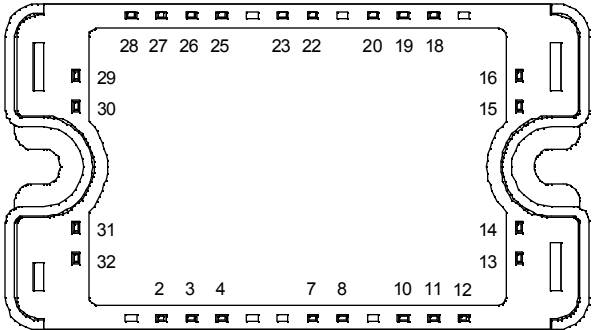
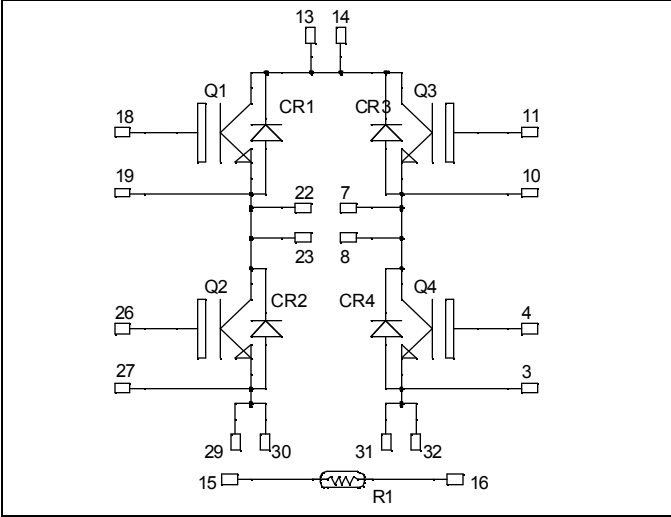


**Full - Bridge
PT IGBT Power Module**

**$V_{CES} = 1200V$
 $I_C = 30A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7® Punch Through (PT) IGBT
 - Low conduction loss
 - Ultra fast tail current shutoff
 - Low gate charge
 - Switching frequency capability in the 200kHz range
 - Soft recovery parallel diodes
 - Low diode VF
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	45
		$T_c = 80^\circ C$	30
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	105
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	208
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	105A @ 960V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0\text{V}, I_C = 250\mu\text{A}$	1200			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$			250	μA
		$V_{CE} = 1200\text{V}$			2500	
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15\text{V}$		3.3	3.9	V
		$I_C = 30\text{A}$		3.0		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1\text{mA}$	3		6	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		3240		pF	
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		248			
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		31			
Q_g	Total gate charge	$V_{GE} = 15\text{V}$		150		nC	
Q_{ge}	Gate - Emitter Charge	$V_{Bus} = 600\text{V}$		21			
Q_{gc}	Gate - Collector Charge	$I_C = 30\text{A}$		62			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 30\text{A}$ $R_G = 5\Omega$		16		ns	
T_r	Rise Time			20			
$T_{d(off)}$	Turn-off Delay Time			94			
T_f	Fall Time			40			
E_{on1}	Turn-on Switching Energy				750		μJ
E_{on2}	Turn-on Switching Energy ①				1305		
E_{off}	Turn-off Switching Energy ②				680		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 30\text{A}$ $R_G = 5\Omega$		16		ns	
T_r	Rise Time			20			
$T_{d(off)}$	Turn-off Delay Time			147			
T_f	Fall Time			75			
E_{on1}	Turn-on Switching Energy				750		μJ
E_{on2}	Turn-on Switching Energy ①				2132		
E_{off}	Turn-off Switching Energy ②				1744		

① E_{on2} includes diode reverse recovery

② In accordance with JEDEC standard JESD24-1

Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		68		$k\Omega$
$B_{25/85}$	$T_{25} = 298.16\text{K}$		4080		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T : Thermistor value at T

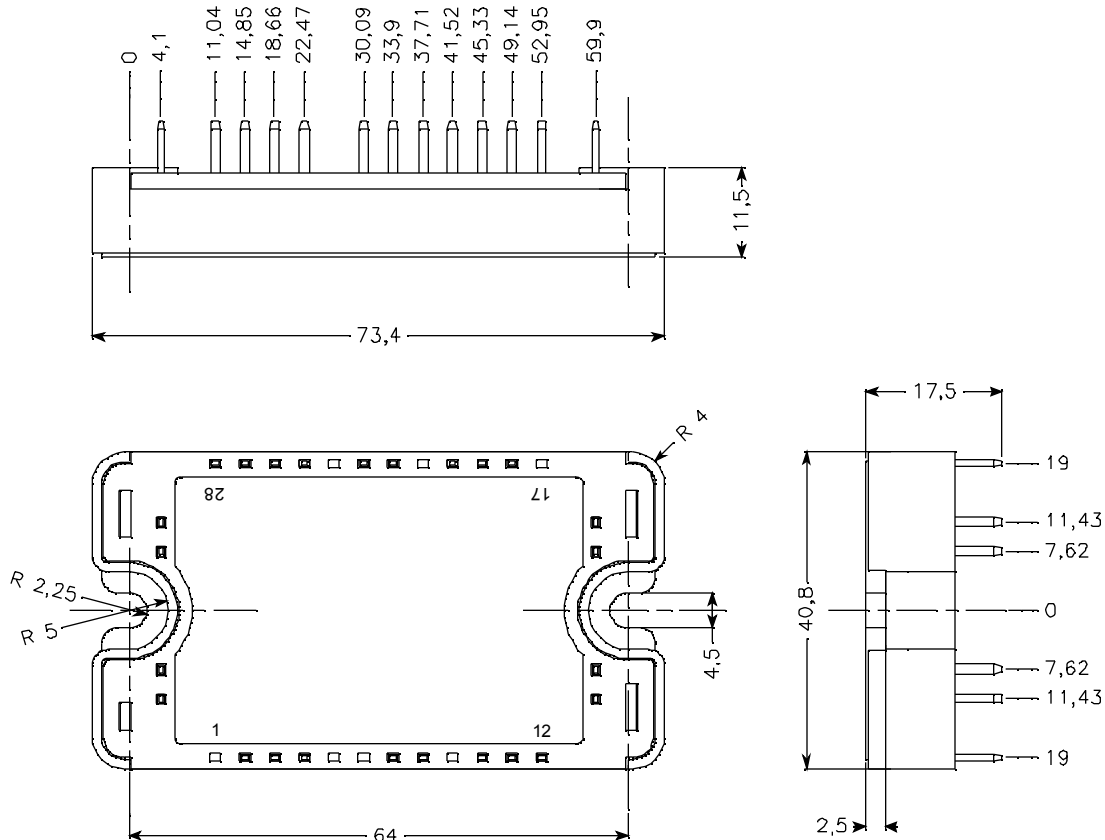
Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	T _j = 25°C			250	μA
			T _j = 125°C			500	
I _{F(AV)}	Maximum Average Forward Current	50% duty cycle	T _c = 80°C		25		A
V _F	Diode Forward Voltage	I _F = 25 A V _{GE} = 0V	T _j = 25°C		2.3	2.8	V
			T _j = 125°C		1.8		
t _{rr}	Reverse Recovery Time	I _F = 25 A V _R = 600V di/dt = 800A/μs	T _j = 125°C		0.13		μs
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		2.3		μC
		T _j = 125°C		6			

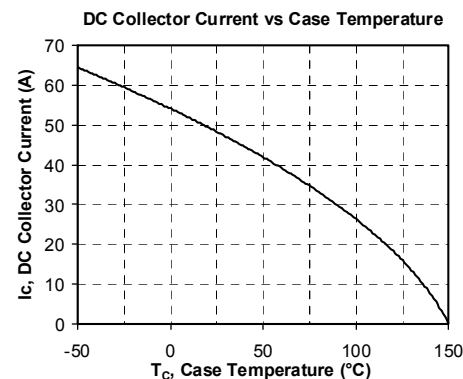
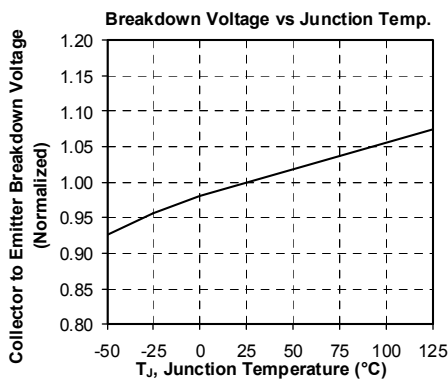
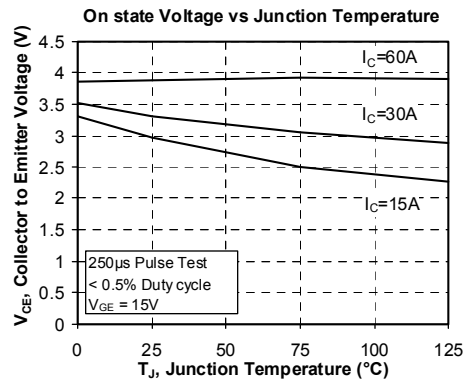
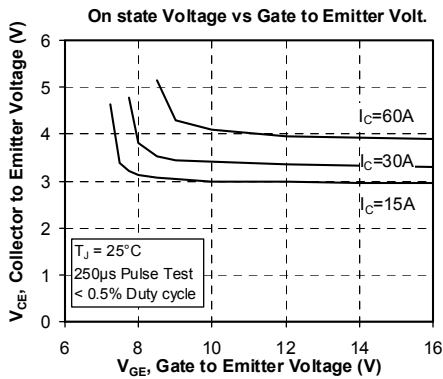
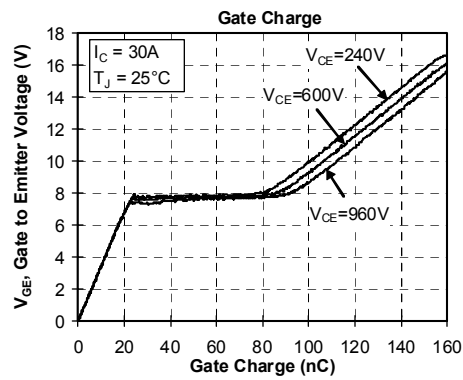
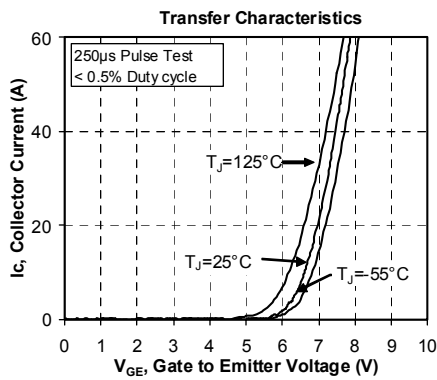
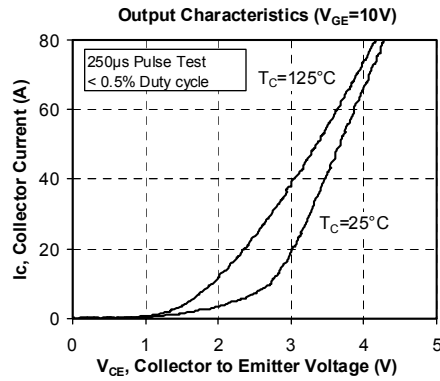
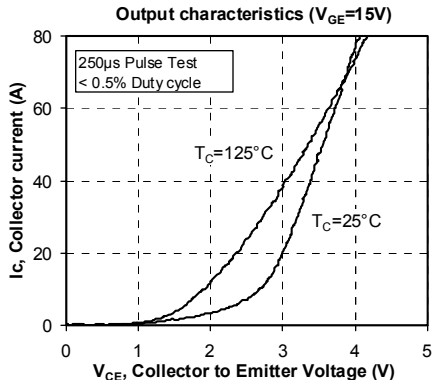
Thermal and package characteristics

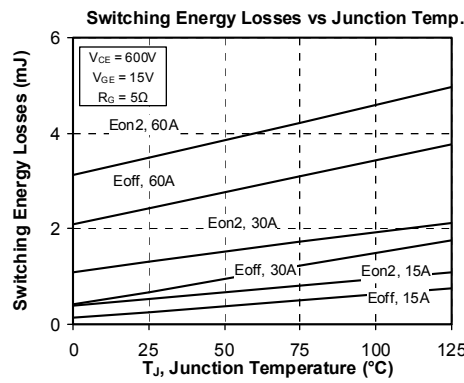
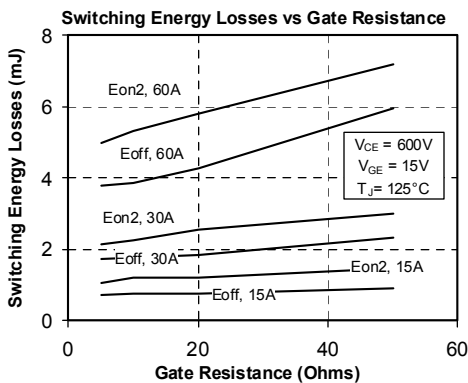
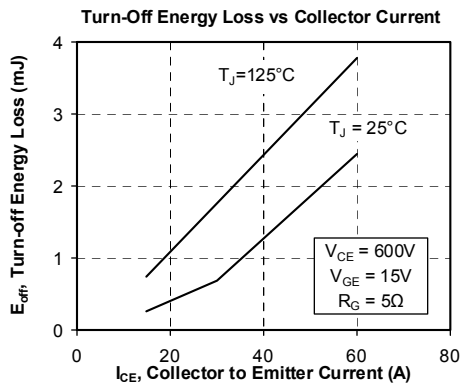
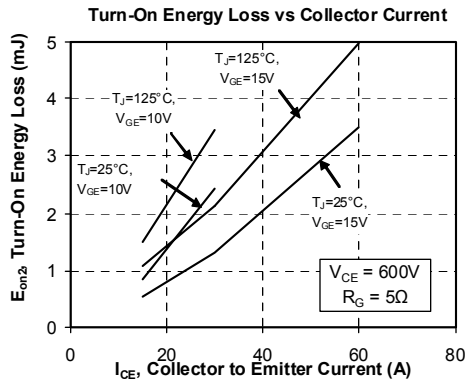
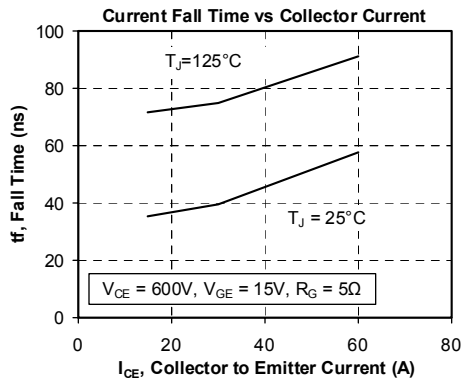
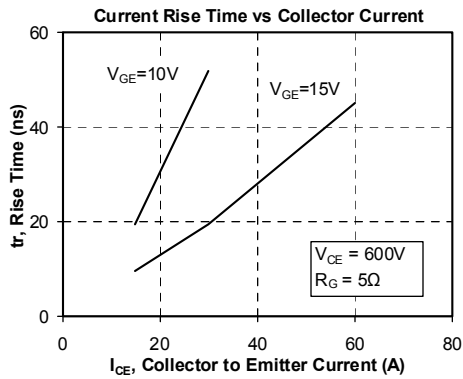
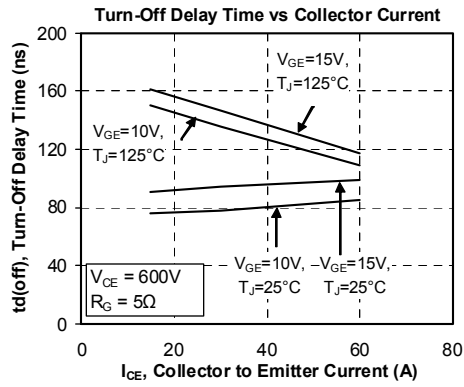
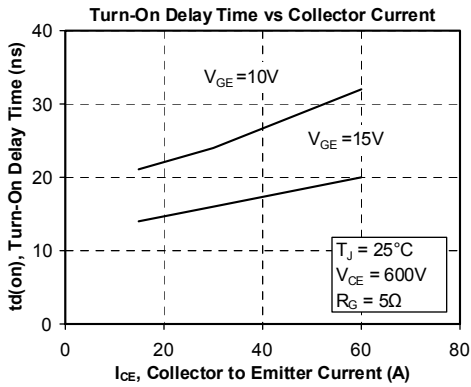
Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case	IGBT				0.6	°C/W
		Diode				1	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4			4.7	N.m
Wt	Package Weight					110	g

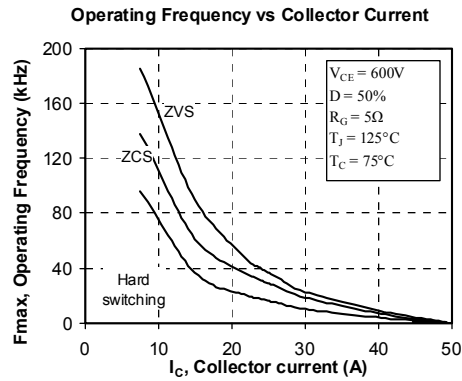
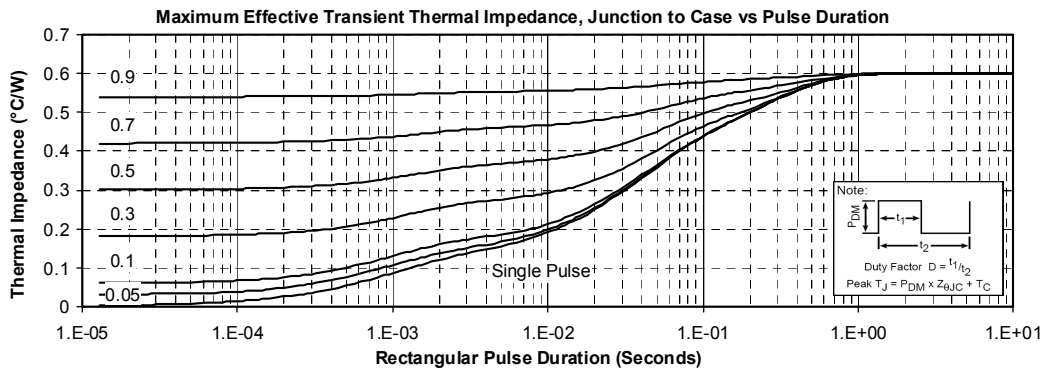
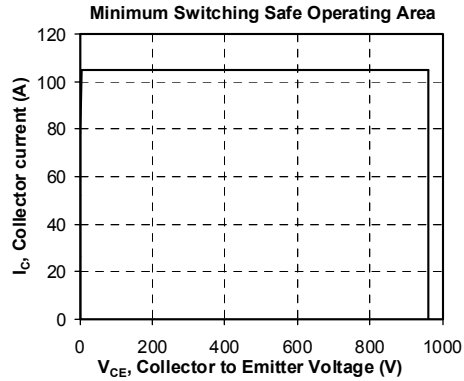
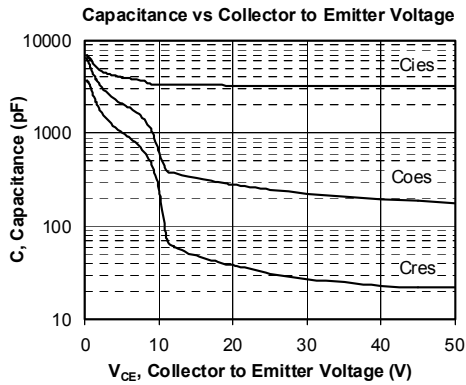
Package outline



Typical Performance Curve







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APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.